

ABSTRACT**Process for fabricating a strained layer**

The present description concerns a method of manufacturing a strained metal or semiconductor or insulating layer comprising a step during which the metal or semiconductor or insulating layer (11) is transferred from a first support substrate (10) to a second support substrate (20), the support substrates (10, 20) having different coefficient of thermal expansions, the transfer step being carried out at high temperature. After removal of the first support substrate (10), the obtained structure is cooled, whereby a tensilely or compressively strained metal or semiconductor or insulating layer (11) is obtained.

(Fig. 1A)